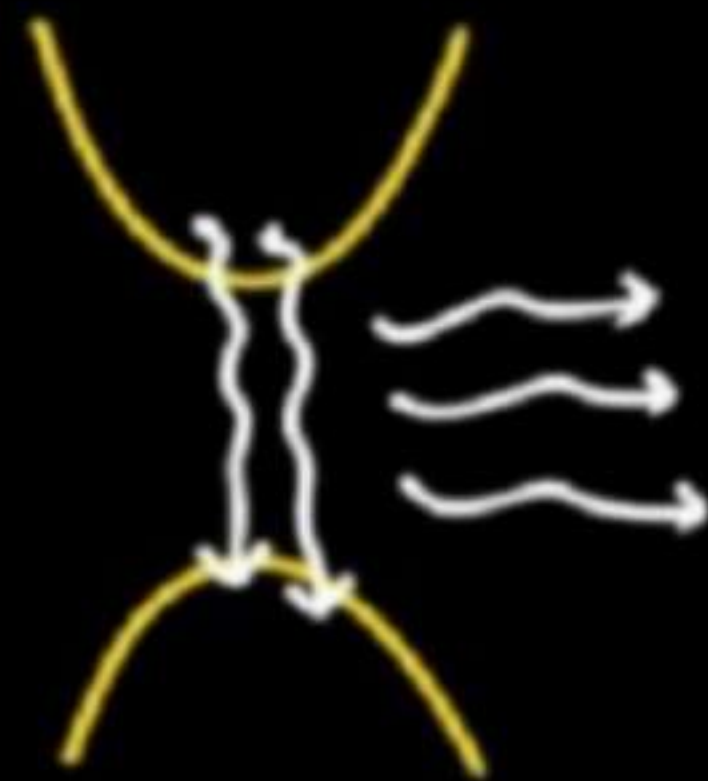


LED  $\rightarrow$  I/P  $\rightarrow$  Electric power.  
 O/P  $\rightarrow$  Light power.  
 Need Direct band gap.

\* Recomb. Must be in the dep. region  
 $\Rightarrow$  Emission from dep. region  
 $\Rightarrow$  F. Biased.



$$h\nu \geq E_g$$

$$\Rightarrow \frac{1.24}{\lambda(\mu\text{m})} \text{ eV} \geq (E_g) \text{ eV}$$

\* Emission @ only one  $\lambda$   
 $\rightarrow$  Monochromatic.  
 [LED is Not Monochromatic].


For proper & good  
Recombinations LED is made  
up of Material which has quantum  
well.

GaAs
InGaAs
GaAs

Smaller E<sub>g</sub> than GaAs

Quantum  
Well.



So an Electron in a well  
is  tough to Escape  
Outside.



$$\therefore V_D \approx V_{bi} = \frac{kT}{q} \log_e \left| \frac{N_D N_A}{n_i^2} \right|$$

$$\therefore n_i^2 = A_0 T^3 \exp \left( \frac{-E_{G_0}}{kT} \right)$$

$$\therefore E_{G_0} \propto 1/\lambda$$

gf  $\lambda \rightarrow$  high

$\Rightarrow E_G \downarrow \rightarrow n_i \uparrow \rightarrow V_D \downarrow$

$\therefore \lambda \rightarrow$  high  
 $\Rightarrow V_D \downarrow$

Since we know  
Rate of Recombination  $\propto \frac{1}{\text{lifetime}}$

$$\Rightarrow R_{\text{rad}} \propto \frac{1}{\tau_{\text{rad}}}$$

$$R_{\text{nonrad}} \propto \frac{1}{\tau_{\text{nonrad}}}$$

$\therefore$  less  $\tau \Rightarrow$  More  
Prob. for light

$\Rightarrow$  Shorter life time  
Indicates  
More recombination.



$$\frac{\text{O/p Optical power}}{\text{I/p Electric power}} = \frac{P_{\text{opt}}}{P_{\text{in}}} \rightarrow \text{Radiative Efficiency.}$$

(Wall plug Efficiency).  
(WPE).

$$\frac{\text{Number of Photons Emitted (into free space per second)}}{\text{Number of Carriers injected by Electric power Supply}} = \text{External Quantum Efficiency [EQE].}$$

$$\text{EQE} = \frac{P_o / hc / \lambda}{P_{\text{in}} / qV} = \frac{P_o}{P_{\text{in}}} \times \frac{q\lambda}{hc} \times V$$

$$\therefore \frac{\text{EQE}}{\text{WPE}} = \left( \frac{q\lambda}{hc} \right) V \geq 1$$

$\text{if } \theta_i < \theta_c \rightarrow \text{light comes out}$   
 $\text{if } \theta_i > \theta_c \rightarrow \text{light reflects back.}$

if Recombination Occurs After Completion of life time  
 $\rightarrow$  Emission of light is called  
 Spontaneous Emission (LEO).

if Recombination Occurs before Completion of life time  
 during an External disturbance of injected photon  
 $\rightarrow$  Stimulated Emission (LASER).



S.MMTRINATH

How many photons are generated internally & how many come out  
→ Extraction Efficiency.

If generated photons break C-Bond's → light is wasted.

Due to Refractive index,  $\exists$  Internal reflections  $\Rightarrow$  light may not come out.

$\therefore$  Need Fiber Dome type.

How many Recombinations are Radiative  $\rightarrow$  Internal Radiative Efficiency.

$$\frac{(\text{Number of Photons Emitted from Active Region per Second})}{(\text{Number of Electrons injected in to LED per Second})}$$

$$\therefore \eta_{\text{int}} = \frac{P_{\text{int}} \times \lambda}{hcI}$$

$I \rightarrow$  Current through LED.



Total Carrier Recombination life time,

$$\frac{1}{\tau} = \frac{1}{\tau_r} + \frac{1}{\tau_{nr}}$$

+ q Since we know,  $V_D \approx V_{bi} = \frac{kT}{q} \log_e \left| \frac{N_D N_A}{n_i^2} \right|$

& Also,  $n_i^2 = A_0 T^3 \exp\left(\frac{-E_{go}}{kT}\right)$

& As  $\lambda \propto 1/E_g \left[ \because \frac{hc}{\lambda} \gg E_g \right]$

$\Rightarrow$  If  $\lambda \rightarrow \text{high} \Rightarrow E_g \text{ low} \Rightarrow n_i^2 \text{ high} \Rightarrow V_D \downarrow \downarrow$

